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Application Number	See Attached Schedule
Filing Date	See Attached Schedule
First Named Inventor	See Attached Schedule
Art Unit	See Attached Schedule
Examiner Name	See Attached Schedule
Attorney Docket Number	See Attached Schedule

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☒ Assignee of record of the entire interest. See 37 CFR 3.71.
Statement under 37 CFR 3.73(b) is enclosed. (Form PTO/SB/96)

SIGNATURE of Applicant or Assignee of Record

Signature

Name

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Date

Feb. 28, 2007

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NOTE: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required. Submit multiple forms if more than one signature is required, see below*.

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Patent Application Schedule

<u>Attorney Docket</u>	<u>Inventor Name</u>	<u>Status</u>	<u>Appln Serial No.</u>	<u>Title of the Invention</u>
2959P	Pakala, Mahendra	Pending Filed on 11/14/2003	10/714,357	STRESS ASSISTED CURRENT DRIVEN SWITCHING FOR MAGNETIC MEMORY APPLICATIONS
3037D	Nguyen, Paul	Pending Filed on 3/13/2007	11/685,723	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3066C	Nguyen, Paul	Pending Filed on 9/30/2005	11/239,969	SPIN TRANSFER MAGNETIC ELEMENT WITH FREE LAYERS HAVING HIGH PERPENDICULAR ANISOTROPY AND IN-PLAN EQUILIBRIUM MAGNETIZATION
3230C	Diao, Zhitao	Pending Filed on 1/29/2007	11/699,160	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3352P	Pakala, Mahendra	Pending Filed on 12/5/2005	11/294,766	METHOD AND SYSTEM FOR PROVIDING A HIGHLY TEXTURED MAGNETORESISTANCE ELEMENT AND MAGNETIC MEMORY
3557P	Diao, Zhitao	Pending Filed on 6/8/2005	11/147,944	FAST MAGNETIC MEMORY DEVICES UTILIZING SPIN TRANSFER AND MAGNETIC ELEMENTS USED THEREIN
3615P	Huai, Yiming	Pending Filed on 7/1/2005	11/173,087	MAGNETIC ELEMENTS HAVING A BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS
3628P	Apalkov, Dmytro	Pending Filed on 7/19/2005	11/185,507	MAGNETIC ELEMENTS HAVING IMPROVED SWITCHING CHARACTERISTICS AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS
3667P	Pakala, Mahendra	Pending Filed on 8/23/2005	11/210,452	SPIN-TRANSFER SWITCHING MAGNETIC ELEMENTS USING FERRIMAGNETS AND MAGNETIC MEMORIES USING THE MAGNETIC ELEMENTS
3671P	Chen, Eugene	Pending Filed on 8/31/2005	11/217,258	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS

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3691P	Chen, Eugene	Pending Filed on 8/31/2005	11/217,524	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS
3709P	Apalkov, Dmytro	Pending Filed on 10/14/2005	11/251,428	SPIN TRANSFER BASED MAGNETIC STORAGE CELLS UTILIZING GRANULAR FREE LAYERS AND MAGNETIC MEMORIES USING SUCH CELLS
3725P	Chen, Eugene	Pending Filed on 10/27/2005	11/260,778	Current Driven Switched Magnetic Storage Cells Having Improved Read and Write Margins and Magnetic Memories Using Such Cells
3753P	Chen, Eugene	Pending Filed on 2/24/2006	11/361,267	CURRENT DRIVEN MEMORY CELLS HAVING ENHANCED CURRENT AND ENHANCED CURRENT SYMMETRY
3846P	Luo, Xiao	Pending Filed on 5/18/2006	11/436,446	High Density Magnetic Memory Cell Layout for Spin Transfer Torque Magnetic Memories Utilizing Donut Shaped Transistors
3850P	Luo, Xiao	Pending Filed on 6/1/2006	11/446,391	METHOD AND SYSTEM FOR PROVIDING A MAGNETIC MEMORY STRUCTURE UTILIZING SPIN TRANSFER
3856CIP	Ding, Yunfei	Pending Filed on 4/17/2007	11/736,290	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3856P	Ding, Yunfei	Pending Filed on 7/17/2006	11/487,723	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3861P	Chen, Eugene	Pending Filed on 6/26/2006	11/476,171	Current Driven Switching of Magnetic Storage Cells Utilizing Spin Transfer and Magnetic Memories Using Such Cells Having Enhanced Read and Write Margins
3887CIP	Huai, Yiming	Pending Filed on 9/20/2006	11/523,872	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING
3887P	Huai, Yiming	Pending Filed on 7/14/2006	11/487,552	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING

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3958P	Wang, Lien-Chang	Pending Filed on 10/30/2006	11/589,347	METHOD AND SYSTEM FOR PROVIDING A CONTACT TO A MAGNETIC ELEMENT IN A MEMORY
4025P	Diao, Zhitao	Pending Filed on 3/27/2007	11/692,090	METHOD AND SYSTEM FOR PROVIDING FIELD BIASED MAGNETIC MEMORY DEVICES
4090P	Li, Zhanjie	Pending Filed on 4/3/2007	11/695,614	METHOD AND SYSTEM FOR PROVIDING DOMAIN WALL ASSISTED SWITCHING OF MAGNETIC ELEMENTS AND MAGNETIC MEMORIES USING SUCH MAGNETIC ELEMENTS
2929P	Huai, Yiming	Allowed	10/839,064	MAGNETORESISTIVE ELEMENT HAVING REDUCED SPIN TRANSFER INDUCED NOISE
2990D	Huai, Yiming	Allowed	11/413,744	Magnetic Elements with Ballistic Magnetoresistance Utilizing Spin-Transfer and an MRAM Device Using Such Magnetic Elements
3008C	Nguyen, Paul	Allowed	11/256,387	Magnetic Element Utilizing Spin-Transfer and Half-Metals and an MRAM Device Using the Magnetic Element
3037P	Nguyen, Paul	Allowed	10/783,416	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3095P	Huai, Yiming	Allowed	10/829,313	SPIN TRANSFER MAGNETIC ELEMENTS WITH SPIN DEPOLARIZATION LAYERS
3230P	Diao, Zhitao	Allowed	10/938,219	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3399P	Huai, Yiming	Allowed	11/027,397	MTJ ELEMENTS WITH HIGH SPIN POLARIZATION LAYERS CONFIGURED FOR SPIN-TRANSFER SWITCHING AND SPINTRONICS DEVICES USING THE MAGNETIC ELEMENTS
3648P	Wang, Lien-Chang	Allowed	11/192,811	MAGNETIC DEVICES HAVING A HARD BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC DEVICES